

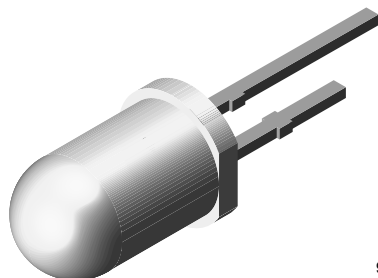


# THE DATASHEET OF TSHF5210





## High Speed Infrared Emitting Diode, 890 nm, Surface Emitter Technology



94 8390

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Leads with stand-off
- Peak wavelength:  $\lambda_p = 890$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 8^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

### DESCRIPTION

TSHF5210 is an infrared, 890 nm emitting diode based on surface emitter chip technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\phi$ (°)	$\lambda_p$ (nm)	$t_r$ (ns)
TSHF5210	327	$\pm 8$	890	10

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHF5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5$ , $t_p = 100$ $\mu\text{s}$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100$ $\mu\text{s}$	$I_{FSM}$	1	A
Power dissipation		$P_V$	170	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Ambient temperature range		$T_{amb}$	-40 to +85	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-40 to +100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction to ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	230	K/W

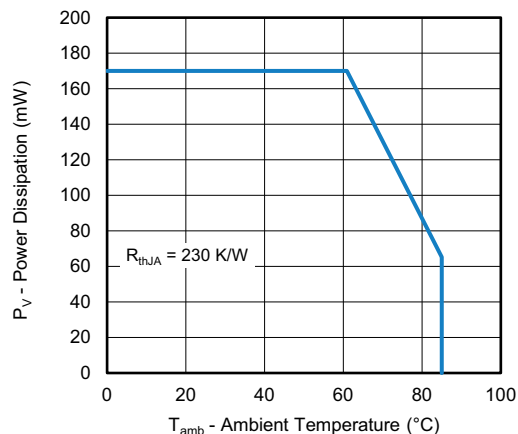


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

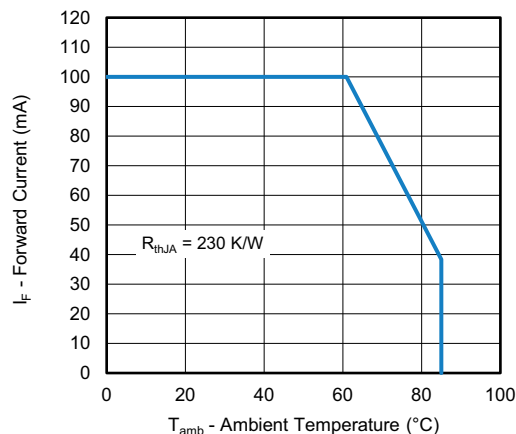


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>	-	1.5	1.7	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>	-	3	-	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	TK <sub>V<sub>F</sub></sub>	-	-1.3	-	mV/K
Reverse current		I <sub>R</sub>	Not designed for reverse operation			μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0 mW/cm <sup>2</sup>	C <sub>j</sub>	-	55	-	pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	I <sub>e</sub>	150	327	450	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	I <sub>e</sub>	-	2700	-	mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	φ <sub>e</sub>	-	53	-	mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 100 mA	TKφ <sub>e</sub>	-	-0.3	-	%/K
Angle of half intensity		φ	-	± 8	-	°
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>	-	890	-	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ	-	40	-	nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>	-	0.3	-	nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>	-	10	-	ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>	-	10	-	ns



**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

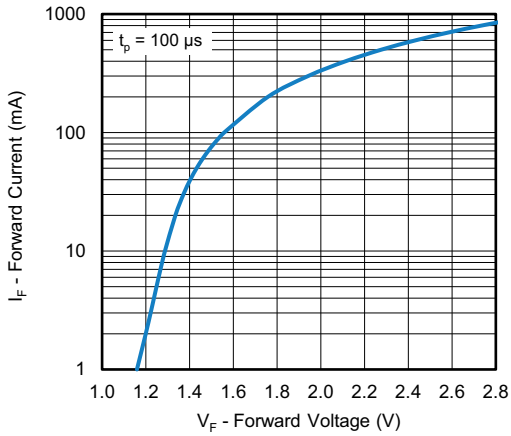


Fig. 3 - Forward Current vs. Forward Voltage

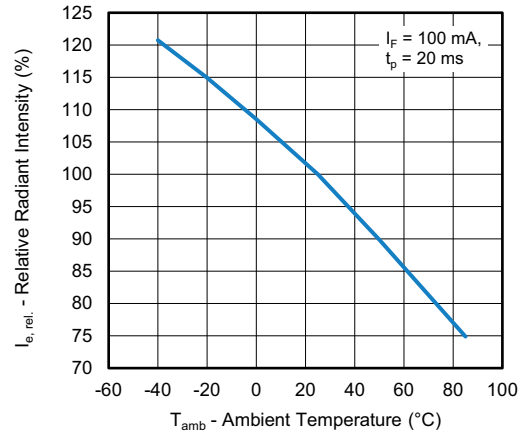


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

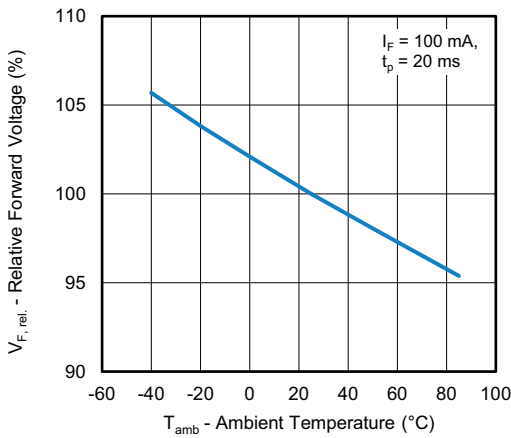


Fig. 4 - Relative Forward Voltage vs Ambient Temperature

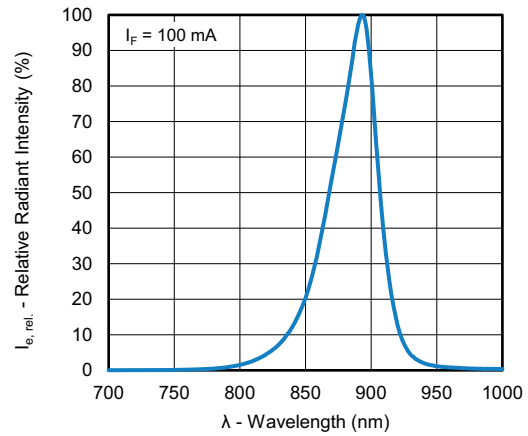


Fig. 7 - Relative Radiant Intensity vs. Wavelength

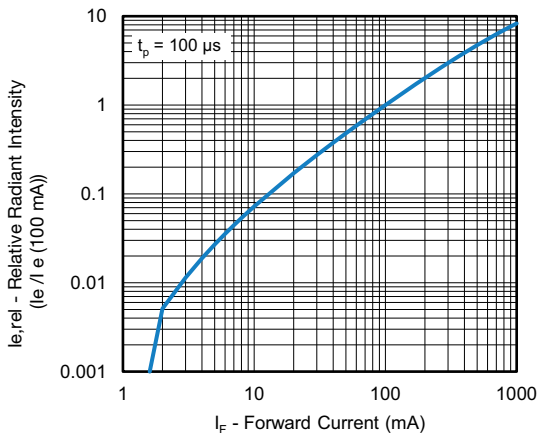


Fig. 5 - Relative Radiant Intensity vs. Forward Current

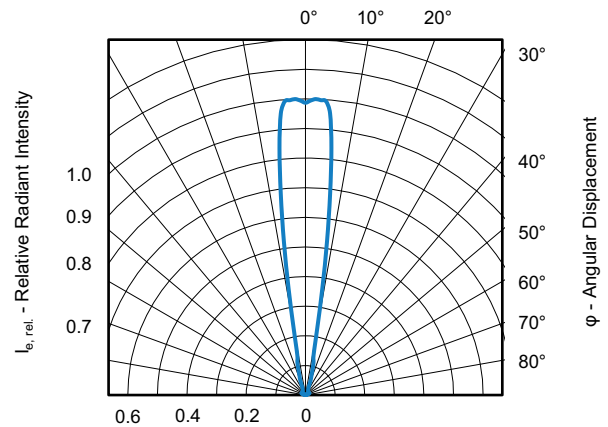
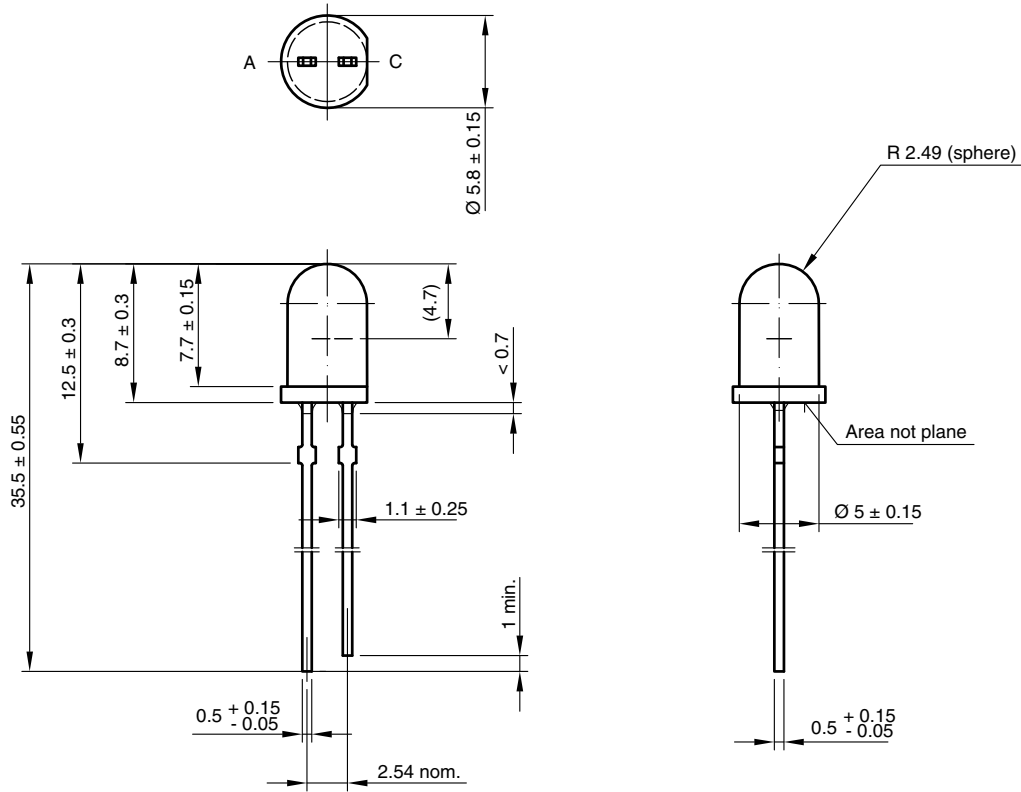


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



**PACKAGE DIMENSIONS** in millimeters



6.544-5258.02-4  
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95 10916



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